PDFN5×6A MOS
Complementary Enhancement MOSFET in a PDFN5 × 6A Plastic Package.

N-channel
V_{DS}(V)=30V
I_D=39.5A
$R_{DS(ON)}$<10mΩ(V_{GS}=10V)
$R_{DS(ON)}$<15mΩ(V_{GS}=4.5V)

P-channel
V_{DS}(V)=-30V
I_D=-39A
$R_{DS(ON)}$<12mΩ(V_{GS}=-10V)
$R_{DS(ON)}$<20mΩ(V_{GS}=-4.5V)

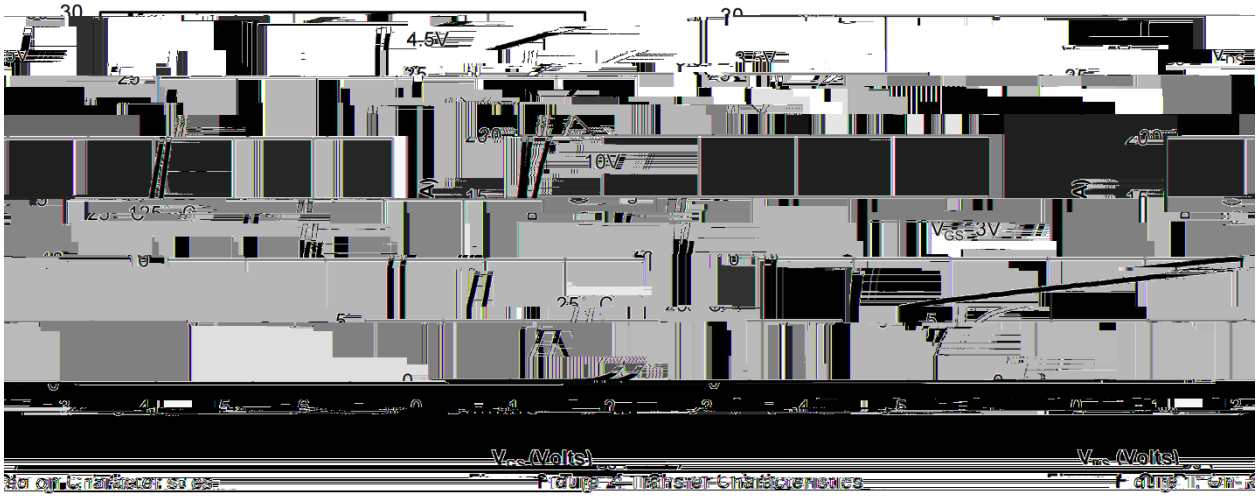
HF Product.

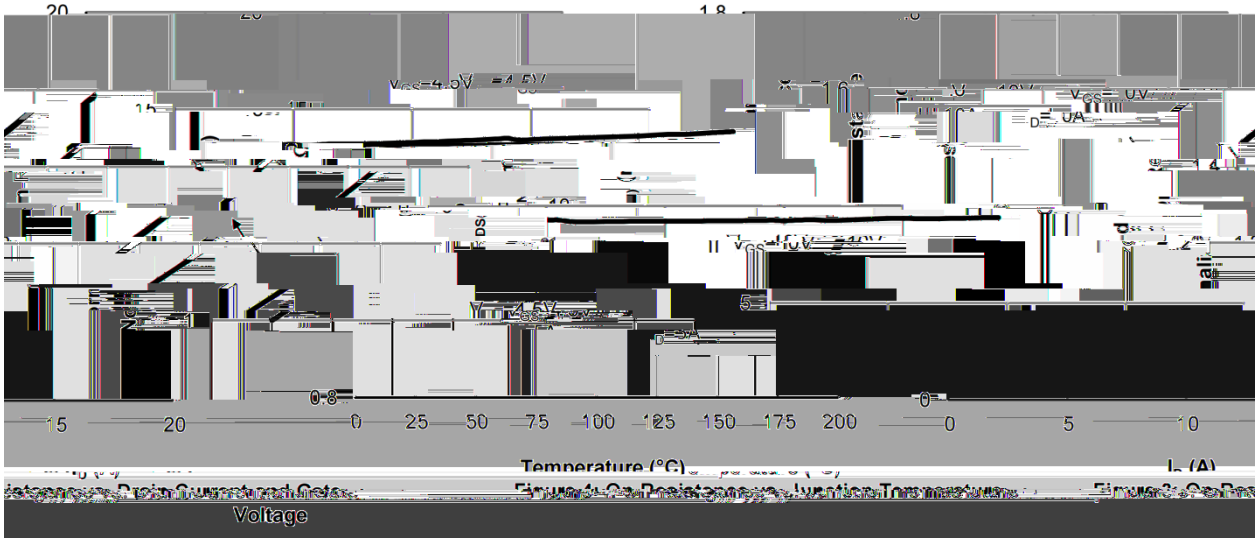
DC/DC
These devices are well suited for 1

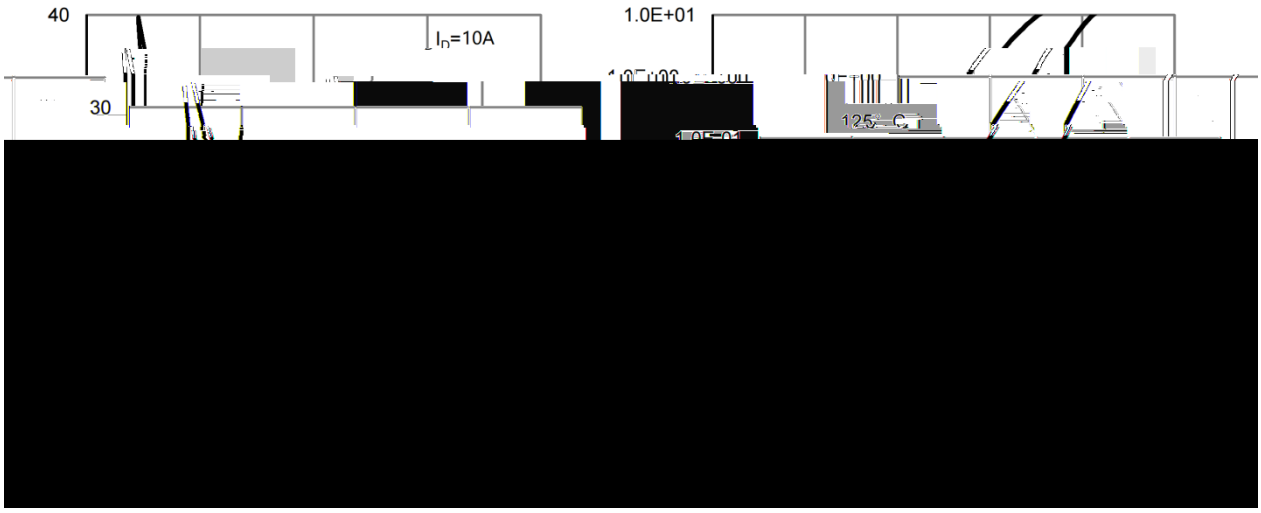
Parameter

BRCS080C03YM

N- / N-CHANNEL Electrical Characteristic Curve



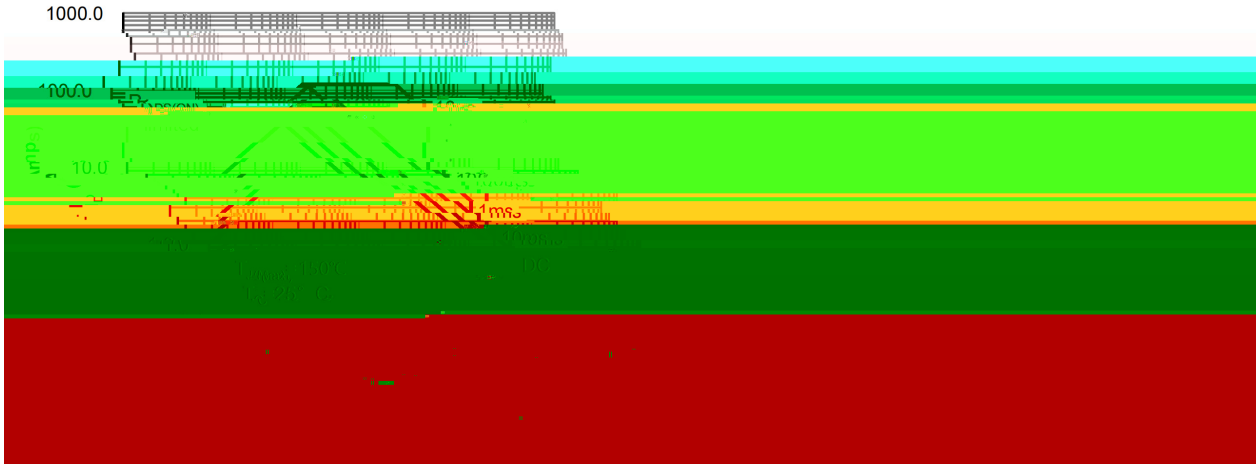


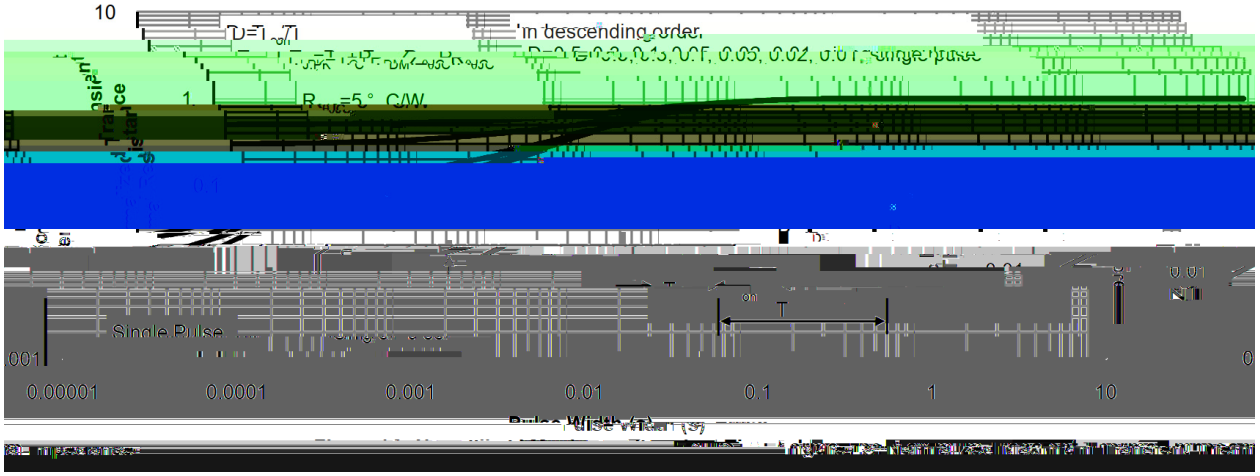


BRCS080C03YM

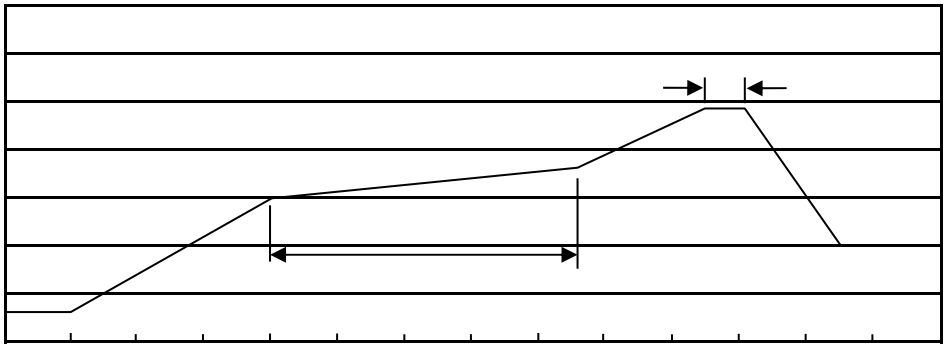
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown						

P- / P-CHANNEL Electrical Characteristic Curve





( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



		Note:
1	150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm³)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
PDFN5×6A	5,000	2	10,000	6	60,000	13''×12	360×360×50	380×335×366

/ Notices